

TRANSISTOR (PNP)

Plastic-Encapsulate Transistor

FEATURES

Power dissipation

$$P_{CM}: 0.625W \text{ (Tamb=25}^{\circ}\text{C)}$$

Collector current

$$I_{CM}: -0.2A$$

Collector-base voltage

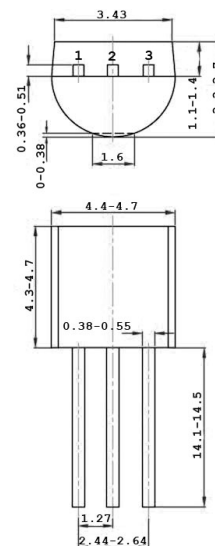
$$V_{(BR)CBO}: -40V$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$

TO-92

1. EMITTER
2. BASE
3. COLLECTOR



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-40V, I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-10mA$	100	300	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-50mA$	60		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-50mA, I_B=-5mA$		-0.4	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-50mA, I_B=-5mA$		-0.95	V
Transition frequency	f_r	$V_{CE}=-20V, I_C=-10mA$ $f=100MHz$	250		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	G
Range	100-200	200-300	300-400